Session Title:	[TB2] Millimeter-Wave Power Amplifiers
Session Date:	December 4 (Thu.), 2025
Session Time:	10:30-12:10
Session Room:	Room B (Halla B)
Session Chair(s):	Chenxi Zhao (University of Electronic Science and Technology of China, China) Inchan Ju (Ajou University, Korea)

[TB2-1] [Invited] 10:30-10:50

Millimeter-Wave CMOS Power Amplifier Designs: Practical Considerations

Hyun-Chul Park (Samsung Electronics, Korea (South))

[TB2-2] 10:50-11:10

GaN Power Amplifier MMICs for Upper D-Band Communications

Philipp Neininger, Thomas Zieciak, Peter Brückner, Michael Mikulla and Rüdiger Quay (Fraunhofer IAF, Germany)

[TB2-3] 11:10-11:30

A Coupler-Based Single-Stage Broadband Ka-Band Power Amplifier with Dual-Driven Gain-Boosting Technique Achieving 21.9 dB/36.4% Gain/PAEmax

Lei Zhang, Weitao Yang, Xiaoxian Liu and Zhangming Zhu (Xidian University, China)

[TB2-4] 11:30-11:50

A Linearity-Improved Millimeter-Wave GaN Power Amplifier Based on AM/PM Compensation

Gaojing Zhang, Luqi Yu, Yucheng Yu, Peng Chen and Chao Yu (Southeast University, China)

[TB2-5] 11:50-12:10

A Ka-Band Reconfigurable PA-LNA Using Load Modulated Balanced Amplifier

Shaoping Zhang and Chenxi Zhao (University of Electronic Science and Technology of China, China)